



TS13001

High Voltage NPN Transistor

TO-92



Pin assignment:
 1. Emitter
 2. Collector
 3. Base

B_V_{CEO} = 400V
B_V_{CBO} = 500V
I_c = 0.1A

V_{CE}(SAT) = 0.5V @ I_c / I_b = 50mA / 10mA

Features

- ❖ High voltage.
- ❖ High speed switching

Structure

- ❖ Silicon triple diffused type.
- ❖ NPN silicon transistor

Ordering Information

Part No.	Packing	Package
TS13001CT	Bulk	TO-92

Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	500V	V
Collector-Emitter Voltage	V _{CEO}	400V	V
Emitter-Base Voltage	V _{EBO}	9	V
Collector Current	DC	I _c	A
	Pulse		
Collector Power Dissipation	P _D	0.6	W
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _{STG}	- 55 to +150	°C

Note: 1. Single pulse, P_w = 5mS, Duty <= 10%

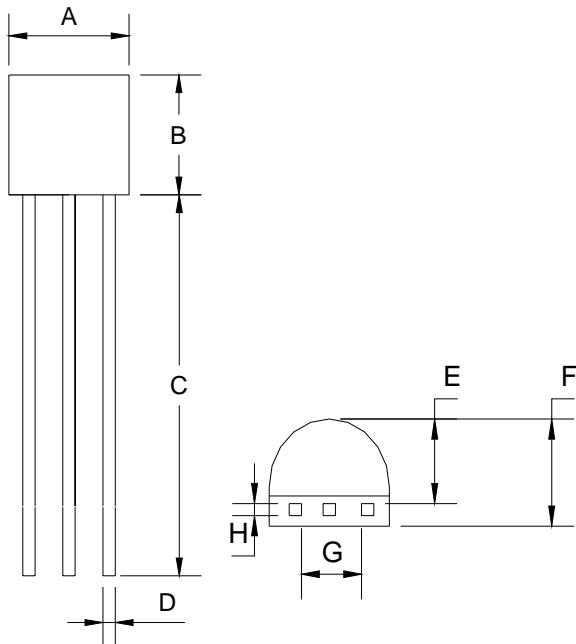
Electrical Characteristics

Ta = 25 °C unless otherwise noted

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Collector-Base Voltage	I _c = 10mA, I _b = 0	BV _{CBO}	500	--	--	V
Collector-Emitter Breakdown Voltage	I _c = 10mA, I _e = 0	BV _{CEO}	400	--	--	V
Emitter-Base Breakdown Voltage	I _e = 1mA, I _c = 0	BV _{EBO}	9	--	--	V
Collector Cutoff Current	V _{CB} = 500V, I _e = 0	I _{CBO}	--	--	100	uA
Emitter Cutoff Current	V _{EB} = 7V, I _c = 0	I _{EBO}	--	--	0.01	uA
Collector-Emitter Saturation Voltage	I _c / I _b = 50mA / 10mA	V _{CE(SAT)}	--	--	0.5	V
DC Current Gain	V _{CE} = 5V, I _c = 20mA	h _{FE}	10	--	40	
Output Capacitance	V _{CB} = 10V, f = 0.1MHz	C _{ob}	--	4	--	pF
Storage Time	V _{CE} = 250V, I _c = 5 mA, I _{b1} =I _{b2} =40mA	ts	--	--	2.0	uS
Fall Time		tf	--	--	0.8	

Note : pulse test: pulse width <=5mS, duty cycle <=10%

TO-92 Mechanical Drawing



DIM	TO-92 DIMENSION		INCHES	
	MILLIMETERS		MIN	MAX
A	4.30	4.70	0.169	0.185
B	4.30	4.70	0.169	0.185
C	14.30(typ)		0.563(typ)	
D	0.43	0.49	0.017	0.019
E	2.19	2.81	0.086	0.111
F	3.30	3.70	0.130	0.146
G	2.42	2.66	0.095	0.105
H	0.37	0.43	0.015	0.017